SPECIFICATION

 Device Name
 : IGBT-IPM

 Type Name
 : 6MBP150RTB060

 Spec. No.
 : MS6M0656

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Fuji Electric Co.,Ltd. Matsumoto Factory

	DATE	NAME	APPROVED	Fuii Floatrio Co Itd	
DRAWN	Jul -8- '02	K.Sekigawa		Fuji Electric Co.,Ltd.	
CHECKED	Jul -3-02	niehiwa	7, Fujiluna	MS6M0656 1/22	<u>a</u>
CHECKED		K. Yame da] /	MS6M0656 1/22	

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Revised Records

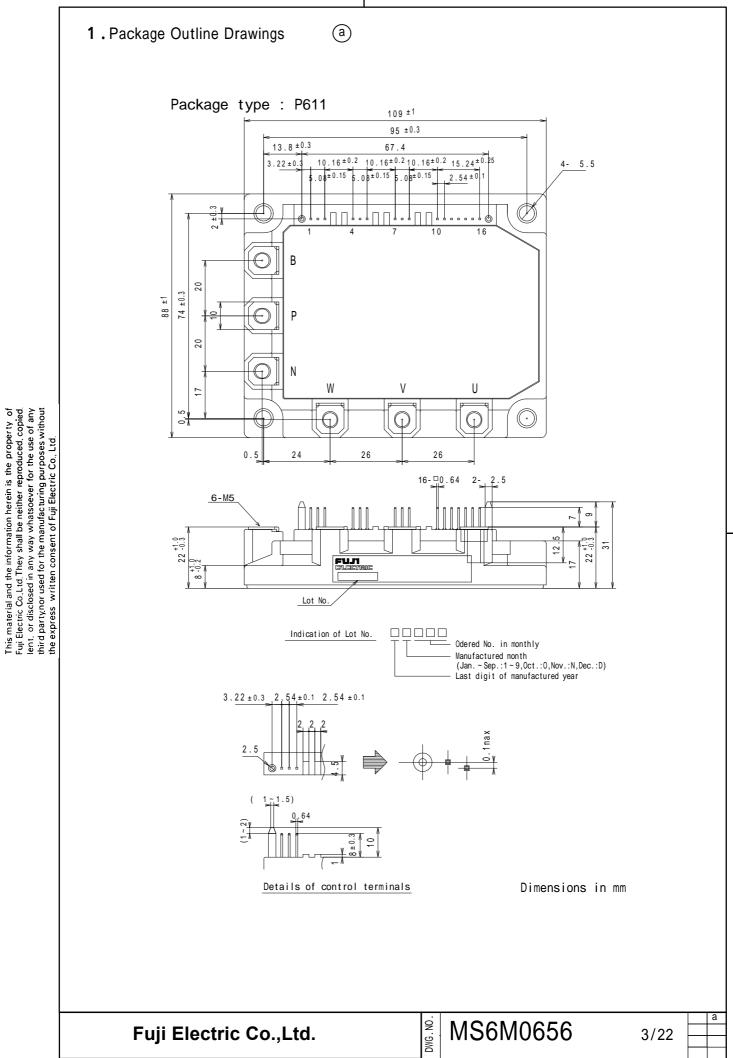
Date	Classi- fication	Ind.	Content	Applied date	Drawn	Check ed	Check ed	Appro ved
Jul-8-62	Enactment			Issued date	K.Sekigawa	(Nishiw to	L. Yamada	7, Fychira
09. Apr. 2003	Revision	а	Reliability Test Items	09.Apr.	V. Tustnala	Tolyada	K. Yawah	7. Fujihilu L.
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2. Pin Descriptions

Main circuit

Symbol	Description
Р	Positive input supply voltage.
U	Output (U).
V	Output (V).
W	Output (W).
N	Negative input supply voltage.
В	No contact.

Control circuit

Symbol	Description
GNDU	High side ground (U).
VinU	Logic input for IGBT gate drive (U).
VccU	High side supply voltage (U).
GNDV	High side ground (V).
VinV	Logic input for IGBT gate drive (V).
VccV	High side supply voltage (V).
GNDW	High side ground (W).
VinW	Logic input for IGBT gate drive (W).
VccW	High side supply voltage (W).
GND	Low side ground.
Vcc	Low side supply voltage.
VinDB	No contact.
VinX	Logic input for IGBT gate drive (X).
VinY	Logic input for IGBT gate drive (Y).
VinZ	Logic input for IGBT gate drive (Z).
ALM	Low side alarm signal output.

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3. Brock Diagram Ρ VccU VinU Pre-Driver **GNDU** U VccV VinV Pre-Driver **GNDV** VccW VinW Pre-Driver **GNDW** W Vcc This material and the information herein is the property of Fuji Electric Co.Ltd. They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third partynor used for the manufacturing purposes without the express written consent of Fuji Electric Co., Ltd. VinX Pre-Driver **GND** VinY Pre-Driver Pre-Driver VinZ NC ●── B → NC \bigcirc N RALM Pre-drivers include following functions Amplifier for driver Short circuit protection Over heating protection **ALM** circuit 1.5k Under voltage lockout circuit Over current protection IGBT chip over heating protection Fuji Electric Co.,Ltd. MS6M0656 5/22

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Tc = 25 unless otherwise specified.

	Items		Symbol	Min.	Max.	Units
		DC	VDC	0	450	V
Bu	s Voltage	Surge	VDC(surge)	0	500	V
(b	etween terminal P and N)	Shortoperating	Vsc	200	400	V
Co	llector-Emitter Voltage *1		Vces	0	600	V
		DC	lc		150	Α
nverter	Collector Current	1ms	Icp		300	Α
l N		Duty68.2% *2	-lc		150	Α
	Collector Power Dissipation	One transistor *3	Pc		431	W
Sup	oply Voltage of Pre-Driver *4		Vcc	-0.5	20	V
Inp	ut Signal Voltage *5		Vin	-0.5	Vcc+0.5	V
Inp	ut Signal Current		lin		3	mA
Ala	rm Signal Voltage *6		VALM	-0.5	Vcc	V
Ala	rm Signal Current *7		IALM		20	mA
Jur	nction Temperature		Tj		150	
Ор	erating Case Temperature		Topr	-20	100	
Sto	orage Temperature		Tstg	-40	125	
Isolating Voltage		Vice		A C 2 E 0 0	V	
(Terminal to base, 50/60Hz sine wave 1min.) *8		Viso		AC2500	V	
Scı	rew Torque	Terminal (M5)			2.5	Nimo
		Mounting (M5)			3.5	Nm

Note

- *1 : Vces shall be applied to the input voltage between terminal P and U or V or W or , N and U or V or W.
- *2 : 125 /FWD Rth(j-c)/(lc × VF MAX)=125/0.47/(150 × 2.6) × 100=68.2%
- *3 : Pc=125 /IGBT Rth(j-c)=125/0.29=431W [Inverter]
- *4: VCC shall be applied to the input voltage between terminal No.3 and 1, 6 and 4, 9 and 7, 11 and 10
- *5: Vin shall be applied to the input voltage between terminal No.2 and 1, 5 and 4, 8 and 7, 13,14,15 and 10.
- *6: VALM shall be applied to the voltage between terminal No.16 and 10.
- *7: IALM shall be applied to the input current to terminal No.16.
- *8 : 50Hz/60Hz sine wave 1 minute.

, Vcc = 15V unless otherwise specified.

5.1 Main circuit

	Item	Symbol	Conditi	ons	Min.	Тур.	Max.	Units
	Collector Current at off signal input	ICES	Vce = 600V Vin terminal open.		-	-	1.0	mA
Inverter	Collector-Emitter	\\OF(+)	Tc = 150A	Terminal	-	-	2.3	V
N N	saturation voltage	VCE(sat)	Ic = 150A	Chip	-	1.8	-	V
	Forward voltage of	\ /F	T = 450A	Terminal	-	ı	2.6	٧
	FWD	VF	-Ic = 150A	Chip	-	1.6	-	V
Tu	rn-on time	ton	V _{DC} = 300V, Tj=125		1.2	ı	-	
Tu	rn-off time	toff	Ic = 150A Fig.1	I , Fig.6	-	ı	3.6	
Re	verse recovery time	trr	V _{DC} = 300V IF = 150A Fig	ı.1 , Fig.6	-	-	0.3	us
En	aximum Avalanche ergy non-repetition)	Pav	internal wiring inductance = 50nH Main circuit wiring inductance = 54nH		170	-	-	mJ

5.2 Control circuit

Item	Symbol	Conditions	Min.	Тур.	Max.	Units
Supply current of P-side pre-driver (one unit)	Ісср	Switching Frequency: 0 ~ 15kHz	-	-	18	mA
Supply current of N-side pre-driver	Iccn	Tc = -20 ~ 125 Fig.7	1	-	65	mA
Innut airmal throubald valtage	NC (41)	ON	1.00	1.35	1.70	\/
Input signal threshold voltage	Vin(th)	OFF	1.25	1.60	1.95	V
Input Zener Voltage	Vz	Rin = 20k	1	8.0	-	V
		Tc = -20 Fig.2	1.1	-	-	ms
Alarm Signal Hold Time	tALM	Tc = 25 Fig.2	ı	2.0	-	ms
		Tc = 125 Fig.2	-	-	4.0	ms
Limiting Resistor for Alarm	RALM		1425	1500	1575	

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5.3 Protection Section (Vcc = 15V)

Item	Symbol	Conditions	Min.	Тур.	Max.	Units
Over Current Protection Level of Inverter circuit	loc	Tj=125	225	ı	•	Α
Over Current Protection Delay time	tdoc	Tj=125	-	5	-	us
SC Protection Delay time	tsc	Tj=125 Fig.4	-	-	8	us
IGBT Chips Over Heating Protection Temperature Level	ТјОН	Surface of IGBT Chips	150	-	-	
Over Heating Protection Hysteresis	TjH		-	20	-	
Over Heating Protection Temperature Level	Tc OH	VDC=0V,IC=0A CaseTemperature	110	-	125	
Over Heating Protection Hysteresis	TcH		-	20	-	
Under Voltage Protection Level	VUV		11.0	-	12.5	V
Under Voltage Protection Hysteresis	VH		0.2	0.5	-	

6. Thermal Characteristics (Tc = 25)

Item			Symbol	Min.	Тур.	Max.	Units
Junction to Case	las santan	IGBT	Rth(j-c)	-	-	0.29	
Thermal Resistance *9	Inverter	FWD	Rth(j-c)	1	ı	0.47	/W
Case to Fin Thermal Resistance with Compound			Rth(c-f)	-	0.05	-	

7. Noise Immunity (Vdc=300V, Vcc=15V, Test Circuit Fig 5.)

Item	Conditions	Min.	Тур.	Max.	Units
	Pulse width 1us, polarity ± ,10 minuets Judge: no over-current, no miss operating	± 2.0	-	-	kV
Common mode lightning surge	Rise time 1.2us, Fall time 50us Interval 20s, 10 times Judge: no over-current, no miss operating	± 5.0	-	-	kV

8. Recommended Operating Conditions

Item	Symbol	Min.	Тур.	Max.	Units
DC Bus Voltage	VDC	ı	ı	400	V
Power Supply Voltage of Pre-Driver	Vcc	13.5	15.0	16.5	V
Screw Torque (M5)	-	2.5	-	3.0	Nm

9. Weight

Item	Symbol	Min.	Тур.	Max.	Units
Weight	Wt	-	450	1	g

^{*9: (}For 1device , Case is under the device)

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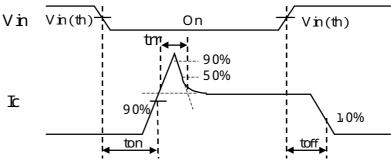
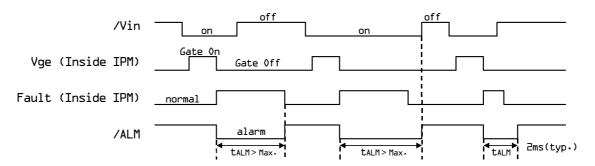


Figure 1. Switching Time Waveform Definitions



Fault: Over-current, Over-heat or Under-voltage

Figure 2. Input/Output Timing Diagram

Necessary conditions for alarm reset (refer to to in figure 2.)

This represents the case when a failure-causing Fault lasts for a period more than tALM. The alarm resets when the input Vin is OFF and the Fault has disappeared.

This represents the case when the ON condition of the input Vin lasts for a period more than tALM. The alarm resets when the Vin turns OFF under no Fault conditions.

This represents the case when the Fault disappears and the Vin turns OFF within tALM. The alarm resets after lasting for a period of the specified time tALM.

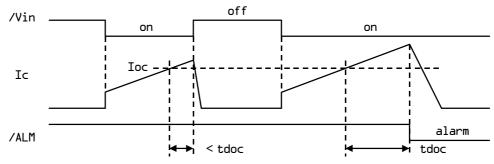


Figure 3. Over-current Protection Timing Diagram

Period: When a collector current over the OC level flows and the OFF command is input within a period less than the trip delay time tdoc, the current is hard-interrupted and no alarm is output.

Period: When a collector current over the OC level flows for a period more than the trip delay time tdoc, the current is soft-interrupted. If this is detected at the lower arm IGBTs, an alarm is output.

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Figure.4 Definition of tsc

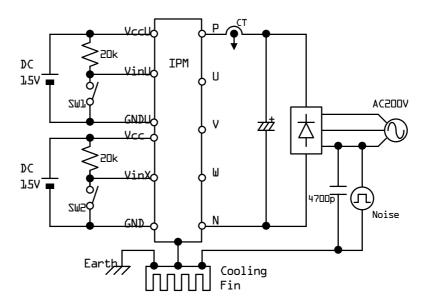


Figure 5. Noise Test Circuit

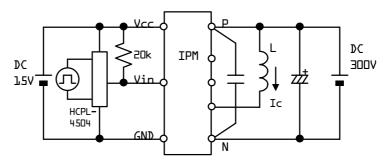


Figure 6. Switching Characteristics Test Circuit

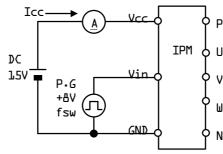


Figure 7. Icc Test Circuit

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10. Truth table

10.1 IGBT Control

The following table shows the IGBT ON/OFF status with respect to the input signal Vin. The IGBT turn-on when Vin is at "Low" level under no alarm condition.

Input (Vin)	Output (IGBT)
Low	ON
High	OFF

10.2 Fault Detection

- (1) When a fault is detected at the high side, only the detected arm stops its output. At that time the IPM dosen't any alarm.
- (2) When a fault is detected at the low side, all the lower arms stop their outputs and the IPM outputs an alarm of the low side.

	F. 14	IGBT			Alarm Output	
	Fault	U-phase	V-phase	W-phase	Low side	ALM
II: ab aida	ОС	0FF	*	*	*	Н
High side	UV	OFF	*	*	*	Н
U-phase	ТjОН	0FF	*	*	*	Н
III ab aida	ОС	*	0FF	*	*	Н
High side	UV	*	0FF	*	*	Н
V-phase	ТjОН	*	0FF	*	*	Н
112 - 1 2 - 1 -	ОС	*	*	0FF	*	Н
High side	UV	*	*	OFF	*	Н
W-phase	ТjОН	*	*	OFF	*	Н
	ОС	*	*	*	0FF	L
Low side	UV	*	*	*	0FF	L
	ТjОН	*	*	*	OFF	L
Case Temperature	ТсОН	*	*	*	OFF	L

^{*:} Depend on input logic.

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11. Cautions for design and application

- 1. Trace routing layout should be designed with particular attention to least stray capacity between the primary and secondary sides of optical isolators by minimizing the wiring length between the optical isolators and the IPM input terminals as possible. フォトカプラとIPMの入力端子間の配線は極力短くし、フォトカプラの一次側と二次側の浮遊容量を小さくした パターンレイアウトにして下さい。
- 2. Mount a capacitor between Vcc and GND of each high-speed optical isolator as close to as possible. 高速フォトカプラの Vcc-GND 間に、コンデンサを出来るだけ近接して取り付けて下さい。
- 3. For the high-speed optical isolator, use high-CMR type one with tpHL, tpLH $0.8 \mu s.$ 高速フォトカプラは tpHL,tpLH 0.8us、高 CMR タイプをご使用ください。
- 4. For the alarm output circuit, use low-speed type optical isolators with CTR 100%. アラーム出力回路は、低速フォトカプラ CTR 100%のタイプをご使用ください。
- 5. For the control power Vcc, use four power supplies isolated each. And they should be designed to reduce the voltage variations.

制御電源 Vcc は 絶縁された4電源を使用してください。また、電圧変動を抑えた設計として下さい。

- 6. Suppress surge voltages as possible by reducing the inductance between the DC bus P and N, and connecting some capacitors between the P and N terminals P-N 間の直流母線は出来るだけ低インダクタンス化し、P-N 端子間にコンデンサを接続するなどしてサージ
 - 電圧を低減して下さい。

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7. To prevent noise intrusion from the AC lines, connect a capacitor of some 4700pF between the three-phase lines each and the ground.

AC ラインからのノイズ侵入を防ぐために、3相各線 - アース間に4700pF程のコンデンサを接続して下さい

- 8. At the external circuit, never connect the control terminal GNDU to the main terminal U-phase, GNDV to V-phase, GNDW to W-phase, and GND to N-phase. Otherwise, malfunctions may be caused.
 - 制御端子 GNDUと主端子U根 制御端子 GNDVと主端子V根 制御端子 GNDWと主端子W根 制御端子 GNDと主端子Nを外部回路で接続しないで下さい。誤動作の原因になります。
- 9. Take note that an optical isolator's response to the primary input signal becomes slow if a capacitor is connected between the input terminal and GND.

入力端子-GND 間にコンデンサを接続すると、フォトカプラー次側入力信号に対する応答時間が長くなりま すのでご注意ください。

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10. Taking the used isolator's CTR into account, design with a sufficient allowance to decide the primary forward current of the optical isolator.

フォトカプラの一次側電流は お使いのフォトカプラの CTR を考慮し十分に余裕をもった設計にして下さい。

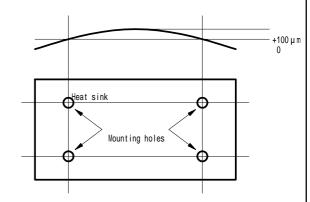
11. Apply thermal compound to the surfaces between the IPM and its heat sink to reduce the thermal contact resistance.

接触熱抵抗を小さくするために、IPMとヒートシンクの間にサーマルコンパウンド塗布して下さい。

12. Finish the heat sink surface within roughness of $10\mu m$ and flatness (camber) between screw positions of 0 to +100 μm . If the flatness is minus, the heat radiation becomes worse due to a gap between the heat sink and the IPM. And, if the flatness is over

 $+100\mu m$, there is a danger that the IPM copper base may be deformed and this may cause a dielectric breakdown.

ヒートシンク表面の仕上げは 粗さ 10um 以下、ネジ位置間での平坦度(反り)は 0~100um として下さい。平坦度がマイナスの場合、ヒートシンクと IPM の間に隙間ができ放熱が悪化します。また、平坦度が+100um 以上の場合IPMの銅



^'-スが変形し絶縁破壊を起こす危険性があります。

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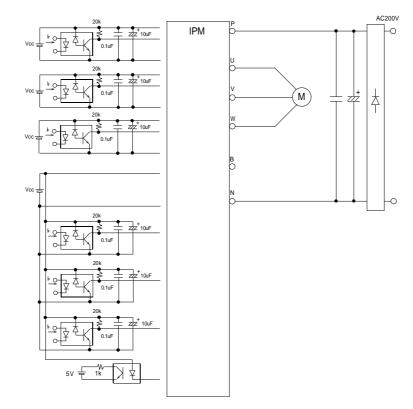
13. This product is designed on the assumption that it applies to an inverter use. Sufficient examination is required when applying to a converter use. Please contact Fuji Electric Co.,Ltd if you would like to applying to converter use.

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14. Please see the "Fuji IGBT-IPM R SERIES APPLICATION MANUAL and "Fuji IGBT MODULES N SERIES N

『富士 IGBT-IPM R シリーズ アプリケーションマニュアル』及び『GBT モジュール N シリーズ アプリケーションマニュアル』を御参照ください。

12. Example of applied circuit 応用回路例



1 3 . Package and Marking 梱包仕様

> Please see the MT6M4140 which is packing specification of P610 & P611 package. P610,611梱包仕様書 MT6M4140を御参照ください。

- 14. Cautions for storage and transportation 保管、運搬上の注意
 - Store the modules at the normal temperature and humidity (5 to 35°C, 45 to 75%). 常温常湿(5~35 、45~75%)で保存して下さい。
 - · Avoid a sudden change in ambient temperature to prevent condensation on the module surfaces. モジュールの表面が結露しないよう、急激な温度変化を避けて下さい。
 - Avoid places where corrosive gas generates or much dust exists. 腐食性ガスの発生場所、粉塵の多い場所は避けて下さい。
 - Store the module terminals under unprocessed conditions モジュールの端子は未加工の状態で保管すること。.
 - Avoid physical shock or falls during the transportation. 運搬時に衝撃を与えたり落下させないで下さい。
- 15. Scope of application 適用範囲

This specification is applied to the IGBT-IPM (type: 6MBP100RTB060). 本仕様書は、IGBT-IPM (型式:6MBP100RTB060)に適用する。

16. Based safety standards 準拠安全規格 **UL1557**

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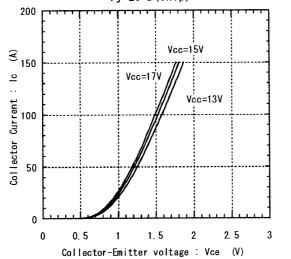
17. Characteristics

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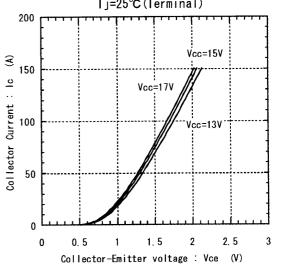
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17-2. Main Circuit Characteristics (Representative)

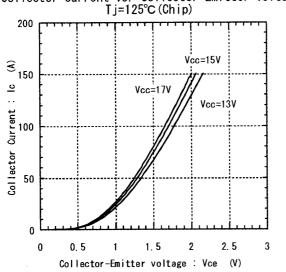
Collector current vs. Collector-Emitter voltage $_{T,j=25^{\circ}C\,(Chip)}$



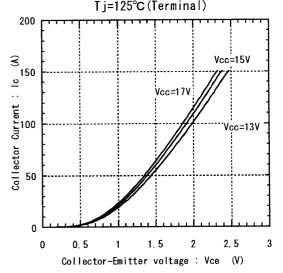
Collector current vs. Collector-Emitter voltage Tj=25°C (Terminal)



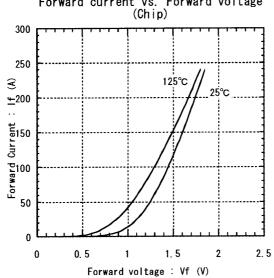
Collector current vs. Collector-Emitter voltage $Tj{=}125^{\circ}C\,(Chip)$



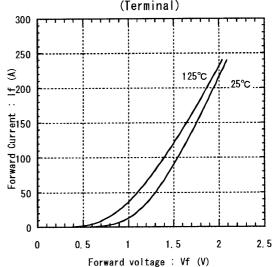
Collector current vs. Collector-Emitter voltage



Forward current vs. Forward voltage



Forward current vs. Forward voltage



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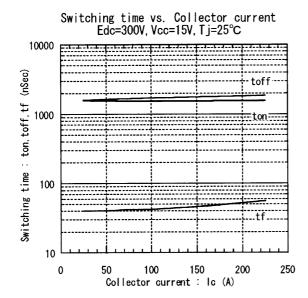
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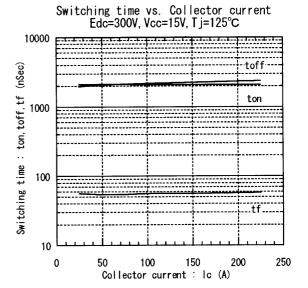
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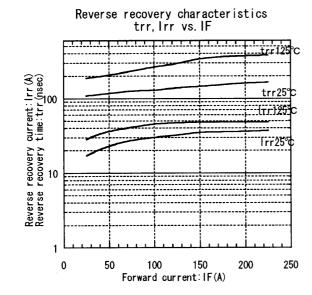
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18. Reliability Test Items

Test cate- gories	Test items		Test methods and conditions		Reference norms EIAJ ED-4701	Number of sample	Accept- ance number
	1	Terminal strength	Pull force	: 40 N (main terminal)	Test Method 401	5	(1:0)
		端子強度 (Pull test)	Test time	10 N (control terminal) : 10 ±1 sec.	Method		
	2	Mounting Strength	Screw torque	: 2.5 ~ 3.5 N· m (M5)	Test Method 402	5	(1:0)
		締付け強度	Test time	: 10 ±1 sec.	method	Ü	(,
	3	Vibration	Range of frequency	: 10 ~ 500 Hz	Test Method 403	5	(1:0)
		振動	Sweeping time	: 15 min.	Condition code B		, ,
			Acceleration	: 100 m/s ²			
sts			Sweeping direction	: Each X,Y,Z axis			
Mechanical Tests			Test time	: 6 hr. (2hr./direction)			
<u>8</u>	4	Shock	Maximum acceleration		Test Method 404	5	(1:0)
l ju		衝擊	Pulse width	1.0 ms	Condition code B		
l ü			Direction	: Each X,Y,Z axis			
Me		0.11	Test time	: 3 times/direction			((0)
-	5	Solderabitlity	Solder temp.	: 235 ±5	Test Method 303	5	(1:0)
		はんだ付け性		: 5.0 ±0.5 sec.	Condition code A		
			Test time	: 1 time be Immersed in solder			
	6	within 1~1.5mm from the body. Resistance to Solder temp. : 260 ±5		Test Method 302	5	(1:0)	
	U	soldering heat	Immersion time	: 10 ±1sec.	Condition code A	3	(1.0)
		はんだ耐熱性	Test time	: 1 time	Condition code A		
		10.7070193		be Immersed in solder			
			within 1~1.5mm from the				
	1	High temperature	Storage temp.	: 125 ±5	Test Method 201	5	(1:0)
		storage 高温保存	Test duration	: 1000 hr.			
	2	Low temperature	Storage temp.	: -40 ±5	Test Method 202	5	(1:0)
		storage 低温保存	Test duration	: 1000 hr.			
	3	Temperature	,	: 85 ±2	Test Method 103	5	(1:0)
		humidity storage	Relative humidity	: 85 ±5%	Test code C		
		高温高湿保存		: 1000hr.			
	4	Unsaturated	Test temp.	: 120 ±2	Test Method 103	5	(1:0)
ا " ا		pressure cooker	Atmospheric pressure		Test code E		
est		プレッシャークッカー	Test humidity	: 85 ±5%			
ment Tests	-	Temperature	Test duration Test temp.	: 96 hr. : Minimum storage temp40 ±5	Test Method 105	5	(1:0)
	5	cycle	rest temp.	Maximum storage temp. 125 ±5	Test Method 105	5	(1.0)
nu		温度サイクル		Normal temp. 5 ~ 35			
/iro		温度ダイブル	Dwell time	: Tmin ~ Tn ~ Tmax ~ Tn			
Environ			Dwen unic	1hr. 0.5hr. 1hr. 0.5hr.			
			Number of cycles	: 100 cycles			
	6	Thermal shock	,	+0	Test Method 307	5	(1:0)
		熱衝擊	Test temp.	: High temp. side 100 ⁻⁵	method		
				+5	Condition code A		
	Fluid used			Low temp. side 0 ⁻⁰			
				: Pure water (running water)			
			Dipping time	: 5 min. par each temp.			
			Transfer time	: 10 sec.			
			Number of cycles	: 10 cycles			

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Test cate- gories	Test items	Te	Reference norms EIAJ ED-4701	of	Accept- ance number	
its	1 High temperature reverse bias 高温逆パイアス	Test temp. Bias Voltage Bias Method Test duration	: Ta = 125 ±5 (Tj 150) : VC = 0.8xVCES : Applied DC voltage to C-E Vcc = 15V : 1000 hr.	Test Method 101	5	(1:0)
Endurance Tests	2 Temperature humidity bias 高温高湿パイアス	Test temp. Relative humidity Bias Voltage Bias Method Test duration	: 85 ±2 : 85 ±5 % : VC = 0.8×VCES Vcc = 15V : Applied DC voltage to C-E : 1000 hr.	Test Method 102 Condition code C	5	(1:0)
	3 Intermitted operating life (Power cycle) 断続動作	ON time OFF time Test temp. Number of cycles	 2 sec. 18 sec. Δ Tj=100 ±5deg Tj 150 , Ta=25 ±5 15000 cycles 	Test Method 106	5	(1:0)

19. Failure Criteria

Item	Charac	teristic	Symbol	Failure criteria		Unit	Note
				Lower limit	Upper limit		
Electrical	Leakage curr	ent	ICES		USL×2	mA	
characteristic	Saturation voltage		VCE(sat)	-	USL×1.2	V	
	Forward volta	ige	VF	-	USL×1.2	V	
	Thermal	IGBT	Rth(j-c)	-	USL×1.2	/W	
	resistance	FWD	Rth(j-c)	-	USL×1.2	/W	
	Over Current Protection Alarm signal hold time Over heating Protection		loc	LSL×0.8	USL×1.2	Α	
			tALM	LSL×0.8	USL×1.2	ms	
			TcOH	LSL×0.8	USL×1.2		
	Isolation voltage		Viso	Broken i	nsulation	-	
Visual	Visual inspection						
inspection			-	The visual sample		-	
	and the ot	hers					

LSL: Lower specified limit. USL: Upper specified limit.

Note: Each parameter measurement read-outs shall be made after stabilizing the components at room ambient for 2 hours minimum, 24 hours maximum after removal from the tests. And in case of the wetting tests, for example, moisture resistance tests, each component shall be made wipe or dry completely before the measurement.

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Warnings

- 1. This product shall be used within its absolute maximum rating (voltage, current, and temperature). This product may be broken in case of using beyond the ratings. 製品の絶対最大定格(電圧,電流,温度等)の範囲内で御使用下さい。絶対最大定格を超えて使用すると、素 子が破壊する場合があります。
- 2. Conect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction. 万一の不慮の事故で素子が破壊した場合を考慮し、商用電源と本製品の間に適切な容量のヒューズ 又はブレーカーを必ず付けて2次破壊を防いでください。
- 3. When studying the device at a normal turn-off action, make sure that working paths of the turn-off voltage and current are within the RBSOA specification. And ,when studying the device duty at a short-circuit current non-repetitive interruption, make sure that the paths are also within the avalanche proof(PAV) specification which is calculated from the snubber inductance, the IPM inner inductance and the turn-off current. In case of use of IGBT-IPM over these specifications, it might be possible to be broken.

通常のターンオフ動作における素子責務の検討の際には、ターンオフ電圧・電流の動作軌跡が RBSOA 仕様内にあることを確認して下さい。また、非繰返しの短絡電流遮断における素子責務の検討に際して は、スナバーインダクタンスとIPM内部インダクタンス及びターンオフ電流から算出されるアバランシェ耐 量(PAV)仕様内である事を確認して下さい。これらの仕様を越えて使用すると、素子が破壊する場合が あります。

- 4. Use this product after realizing enough working on environment and considering of product's reliability life. This product may be broken before target life of the system in case of using beyond the product's reliability life. 製品の使用環境を十分に把握し、製品の信頼性寿命が満足できるか検討の上、本製品を適用して下さ い。製品の信頼性寿命を超えて使用した場合、装置の目標寿命より前に素子が破壊する場合がありま
- 5. If the product had been used in the environment with acid, organic matter, and corrosive gas (For example: hydrogen sulfide, sulfurous acid gas), the product's performance and appearance can not be ensured easily.

酸・有機物・腐食性ガス(硫化水素,亜硫酸ガス等)を含む環境下で使用された場合、製品機能・外観 などの保証は致しかねます。

- 6. Use the product within the power cycle curve (Technical Rep.No.: MT6M4057) 本製品は、パワーサイクル寿命カーブ以下で使用下さい(技術資料 No.: MT6M4057)
- 7. Never add mechanical stress to deform the main or control terminal. The deformed terminal may cause poor contact probrem. 主端子及び制御端子に応力を与えて変形させないで下さい。 端子の変形により、接触不良などを引き起こす 場合があります。

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- 8. According to the outline drawing, select proper length of screw for main terminal. Longer screws may break the case.
 - 本製品に使用する主端子用のネジの長さは、外形図に従い正しく選定下さい。ネジが長いとケースが破損する場合があります。
- 9. If excessive static electricity is applied to the control terminals, the devices can be broken. Implement some countermeasures against static electricity. 制御端子に過大な静電気が印加された場合、素子が破壊する場合があります。取り扱い時は静電気対策を実施して下さい。

Caution

1. Fuji Electric is constantly making every endeavor to improve the product quality and reliability. However, semiconductor products may rarely happen to fail or malfunction. To prevent accidents causing injuly or death, damage to property like by fire, and other social damage resulted from a failure or malfunction of the Fuji Electric semiconductor products, take some measures to keep safety such as redundant design, spread-fire-preventive design, and malfunction-protective design.

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- 2. The application examples described in this specification only explain typical ones that used the Fuji Electric products. This specification never ensure to enforce the industrial property and other rights, nor license the enforcement rights.
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- 3. The product described in this specification is not designed nor made for being applied to the equipment or systems used under life-threatening situations. When you consider applying the product of this specification to particular used, such as vehicle-mounted units, shipboard equipment, aerospace equipment, medical devices, atomic control systems and submarine ralaying equipment or systems, please apply after confirmation of this product to be satisfied about system construction and required reliability.

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